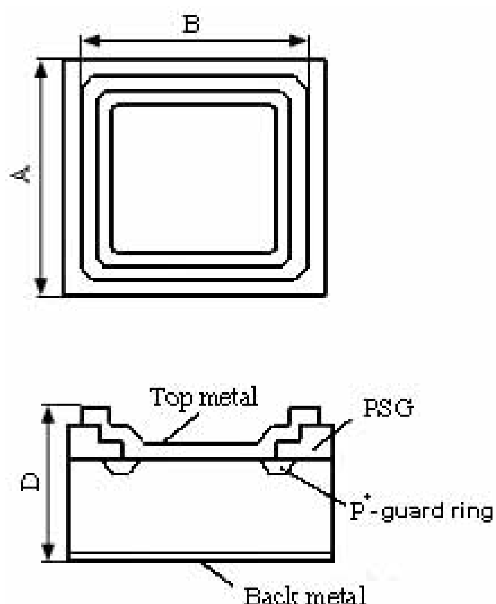
SCHOTTKY DIODES KDS 2127V.

PRELIMINARY

Rev.1. Feb. 2010

VSP-MIKRON	**0,5A/25V. Die Size-39mil.**			
Electrical Characteristics	**Symbol**	**Unit**	**Spec. limit**	**Die Sort**
Breakdown Voltage @ I_R=10mA	V_{BR}	V	28	31
Average Rectified Forward Current	$I_{F(AV)}$	A	0,5	-
DC Forward Voltage @ 25˚C, I_F=0,5A	V_F	V	0,34	0,32 (0,31-typ)
Maximum Reverse Current @ 25˚C, V_R=25V 25˚C, V_R=28V 100˚C, V_R=25V	I_R	mA	0,50 - 15,0	0,40 0,50 15,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	40	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., T_J<125˚C.	I_{RRM}	A	1,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	˚C	125	



DIM	**ITEM**	**µm**
A_X A_y	Wafer Form Die Size	1000 1000
B_X B_y	Top Metal Size	820 820
D	Thickness	300max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;

b) ***Al-Ni-Ag*** – for Soldering.

Backside metal: ***Ti-Ni-Ag***.